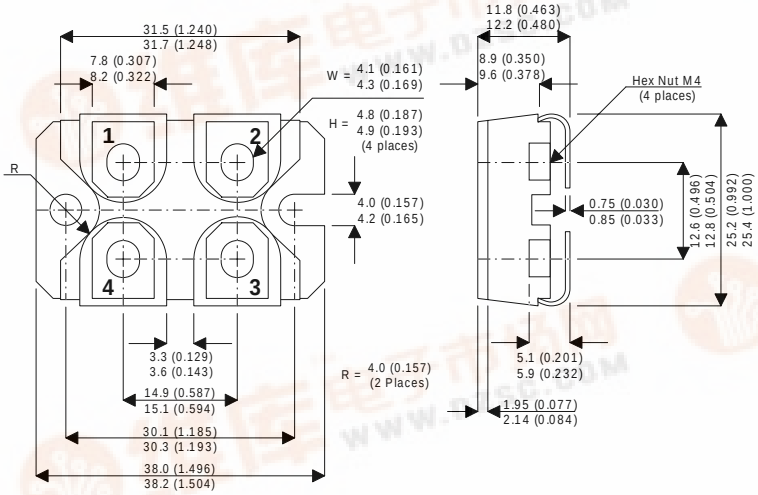
查询BUZ900X4S供应商 捷多邦，专业PCB打样工厂，24小时加急出货

MAGNA TEC

# BUZ900X4S
# BUZ901X4S

**NEW PRODUCT UNDER DEVELOPMENT**

## MECHANICAL DATA
Dimensions in mm (inches)




**SOT227**
Pin 1 – Drain
Pin 2 – Source
Pin 3 – Gate
Pin 4 – Drain

# N–CHANNEL POWER MOSFET

## POWER MOSFETS FOR AUDIO APPLICATIONS

## FEATURES

- HIGH SPEED SWITCHING
- N–CHANNEL POWER MOSFET
- SEMEFAB DESIGNED AND DIFFUSED
- HIGH VOLTAGE (160V & 200V)
- HIGH ENERGY RATING
- ENHANCEMENT MODE
- INTEGRAL PROTECTION DIODE
- P–CHANNEL ALSO AVAILABLE

## ABSOLUTE MAXIMUM RATINGS

($T_{case}$ = 25°C unless otherwise stated)

| | | | BUZ900X4S | BUZ901X4S |
|---|---|---|---|---|
| $V_{DSX}$ | Drain – Source Voltage | | 160V | 200V |
| $V_{GS}$ | Gate – Source Voltage | | ±14V | |
| $I_D$ | Continuous Drain Current | | 32A | |
| $I_{D(PK)}$ | Body Drain Diode | | 32A | |
| $P_D$ | Total Power Dissipation | @ $T_{case}$ = 25°C | 500W | |
| $T_{stg}$ | Storage Temperature Range | | –55 to 150°C | |
| $T_j$ | Maximum Operating Junction Temperature | | 150°C | |
| $R_{\theta JC}$ | Thermal Resistance Junction – Case | | 0.3°C/W | |

找PDF 维库一下 pdf.dzsc.com

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# BUZ900X4S
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## NEW PRODUCT UNDER DEVELOPMENT

## ELECTRICAL RATINGS ($T_{case}$ = 25°C unless otherwise stated)

| | Characteristic | Test Conditions | | Min. | Typ. | Max. | Unit |
|---|---|---|---|---|---|---|---|
| $BV_{DSX}$ | Drain – Source Breakdown Voltage | $V_{GS}$ = –10V | BUZ900X4S | 160 | | | V |
| | | $I_D$ = 10mA | BUZ901X4S | 200 | | | |
| $BV_{GSS}$ | Gate – Source Breakdown Voltage | $V_{DS}$ = 0 | $I_G$ = ±100µA | ±14 | | | V |
| $V_{GS(OFF)}$ | Gate – Source Cut–Off Voltage | $V_{DS}$ = 10V | $I_D$ = 100mA | 0.1 | | 1.5 | V |
| $V_{DS(SAT)}$* | Drain – Source Saturation Voltage | $V_{GD}$ = 0 | $I_D$ = 32A | | | 12 | V |
| $I_{DSX}$ | Drain – Source Cut–Off Current | $V_{GS}$ = –10V | | | | | |
| | | $V_{DS}$ = 160V | BUZ900X4S | | | 10 | mA |
| | | $V_{DS}$ = 200V | BUZ901X4S | | | 10 | mA |
| yfs* | Forward Transfer Admittance | $V_{DS}$ = 10V | $I_D$ = 5A | 2 | | 6 | S |
| $C_{iss}$ | Input Capacitance | $V_{DS}$ = 10V | f = 1MHz | | TBE | | pF |
| $C_{oss}$ | Output Capacitance | | | | TBE | | |
| $C_{rss}$ | Reverse Transfer Capacitance | | | | TBE | | |
| $t_{on}$ | Turn–on Time | $V_{DS}$ = 20V | $I_D$ = 7A | | TBE | | nS |
| $t_{off}$ | Turn-off Time | | | | TBE | | |

* Pulse Test: Pulse Width = 300µS , Duty Cycle ≤ 2%